

IN THE CLAIMS:

The text of all pending claims, (including withdrawn claims) is set forth below. Cancelled and not entered claims are indicated with claim number and status only. The claims as listed below show added text with underlining and deleted text with ~~strikethrough~~. The status of each claim is indicated with one of (original), (currently amended), (cancelled), (withdrawn), (new), (previously presented), or (not entered).

Please **CANCEL** claims 36, 53 and 55, **AMEND** claims 27-29, 37, 38, 43-46 and 54 and **ADD** new claims 56-61 in accordance with the following:

1-26 (Cancelled)

27. (Currently Amended) A system comprising:

an electrical component provided with at least one electrical contact surface;

an electrical insulating layer, which is disposed on the component, the electrical insulating layer having an opening to expose and surround a portion of the contact surface, ~~wherein the insulating layer having a lateral surface that delimits the opening, the electrical insulating layer being formed from at least first and second partial insulating layers having openings with different widths such that a stepped structure is formed from the contact surface to the first partial insulating layer and from the first partial insulating layer to the second partial insulating layer, the lateral surface being formed as part of the stepped structure; and~~

an electrical connecting lead for electrically contacting the contact surface of the component, the electrical connecting lead comprising a first and second metallization layers, the first metallization layer being located on the lateral surface, such that the first metallization layer meets the contact surface at an angle less than 90 degrees, the second metallization layer being formed of a material different from the first metallization layer, the second metallization layer being formed on the insulating layer and outside of the opening in the insulating layer, the second metallization layer having a thickness greater than that of the first metallization layer.

28. (Currently Amended) The system as claimed in claim 27, wherein the first metallization layer is oriented at an angle to the contact surface within a range of from 30° to 80°.

29. (Currently Amended) The system as claimed in claim 27, wherein the first metallization layer has a layer thickness within a range of from 0.5 µm to 30 µm.

30-31. (Cancelled)

32. (Previously Presented) The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 20 μm to 500 μm .

33. (Cancelled)

34. (Previously Presented) The system as claimed in claim 27, wherein the insulating layer is formed by laminating at least one insulating foil onto the component.

35. (Previously Presented) The system as claimed in claim 34, wherein the lateral surface of the insulating layer faces the component, at least one part of the insulating foil is laminated onto the component in such a way that the insulating layer has a surface contour facing away from the component, and a surface contour of the component is shown in the surface contour of the insulating foil that faces away from the component.

36. (Cancelled)

37. (Currently Amended) The system as claimed in claim 36, wherein the second metallization layer ~~section of the connecting lead~~ is electrodeposited.

38. (Currently Amended) The system as claimed in claim 37, wherein the first and/or second metallization layer ~~and/or the section~~ is formed of at least one metal selected from the group consisting of aluminum, gold, copper, molybdenum, silver, titanium and tungsten.

39. (Previously Presented) The system as claimed in claim 36, wherein the component is a semiconductor component.

40. (Previously Presented) The system as claimed in claim 39, wherein the semiconductor component is a power semiconductor component.

41. (Previously Presented) The system as claimed in claim 40, wherein the power semiconductor component is a component selected from the group consisting of a diode, a MOSFET, a IGBT, a thyristor and a bipolar transistor.

42. (Previously Presented) The system as claimed in claim 27, wherein the insulating layer has a plurality of openings arranged in a row or a matrix.

43. (Currently Amended) The system as claimed in claim 27, wherein the first metallization layer is oriented at an angle to the contact surface within a range of from 50° to 70°.

44. (Currently Amended) The system as claimed in claim 27, wherein the first metallization layer has a layer thickness within a range of from 2.0 μm to 20 μm.

45. (Currently Amended) The system as claimed in claim 27, wherein the insulating layer has a layer thickness within a range of from 50 μm up to and including 200 μm.

46. (Currently Amended) A method for producing a system comprising:
providing a component with an electrical contact surface;
producing an insulating layer on the component, the insulating layer having an opening to expose and surround a portion of the contact surface of the component so that the contact surface is freely accessible, the insulating layer having a lateral surface that defines the opening;
and

~~locating-forming~~ a metallization layer of a connecting lead on the lateral surface of the insulating layer in such a way that the metallization layer meets the contact surface at an angle less than 90 degrees, ~~wherein;~~

~~the insulating layer is produced by forming at least first and second partial insulating layers having openings with different widths such that a stepped structure is formed from the contact surface to the first partial insulating layer and from the first partial insulating layer to the second partial insulating layer, the lateral surface being formed as part of the stepped structure.~~

after forming the metallization layer, masking the opening in the insulating layer; and
forming a section of the connecting lead separately from the metallization layer, the section of the connecting lead being produced on the insulating layer while the opening in the insulating layer is masked such that the section of the connecting lead is formed outside of the opening in the insulating layer, the section of the connecting lead having a thickness which

exceeds that of the metallization layer.

47. (Previously Presented) The method as claimed in claim 46, wherein the insulating layer is formed by a process comprising:

laminating at least one insulating foil onto the component; and

producing an opening in the insulating foil so that the contact surface of the component is exposed.

48. (Previously Presented) The method as claimed in claim 47, wherein the insulating foil is laminated under a partial vacuum.

49. (Previously Presented) The method as claimed in claim 47, wherein the opening in the insulating foil is made by laser ablation.

50. (Previously Presented) The method as claimed in claim 46, wherein in order to produce the insulating layer on the component, a compressed air process is used wherein a paint is applied to the component.

51. (Previously Presented) The method as claimed in claim 50, wherein the paint is a photo-sensitive paint.

52. (Previously Presented) The method as claimed in claim 46, wherein the metallization layer and/or the insulating layer is formed by a vapor deposition method.

53. (Cancelled)

54. (Currently Amended) The method as claimed in claim ~~53~~46, wherein a metal is electrodeposited to produce the section on the insulating layer.

55. (Cancelled)

56. (New) The method as claimed in claim 46, wherein the section of the connecting lead is formed from a different material from the metallization layer.

57. (New) The system as claimed in claim 27, wherein the first metallization layer is formed of a titanium tungsten alloy, and the second metallization layer is formed of copper or aluminum.

58. (New) A method for producing a system, comprising:
providing a component on a substrate, the component having an electrical contact surface;
producing an insulating layer on the component, the insulating layer having an opening to expose and surround a portion of the contact surface of the component so that the contact surface is freely accessible, the insulating layer having a lateral surface that defines the opening, the insulating layer being produced by a process comprising:
 laminating a first partial insulating layer on the component and the substrate, the first partial insulating layer having an opening with a first width; and
 laminating a second partial insulating layer on the first partial insulating layer, the second partial insulating layer having an opening with a second width greater than the first width such that a stepped structure is formed from the contact surface to the first partial insulating layer and from the first partial insulating layer to the second partial insulating layer, the lateral surface being formed as part of the stepped structure; and
 locating a metallization layer of a connecting lead on the lateral surface of the insulating layer in such a way that the metallization layer meets the contact surface at an angle less than 90 degrees.

59. (New) The method as claimed in claim 58, wherein the insulating foil is laminated under a partial vacuum.

60. (New) The method as claimed in claim 58, wherein the opening in the insulating foil is made by laser ablation.

61. (New) The method as claimed in claim 58, wherein the metallization layer is formed by a vapor deposition method.